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(54) **GROUP III NITRIDE WAFER AND ITS PRODUCTION METHOD**

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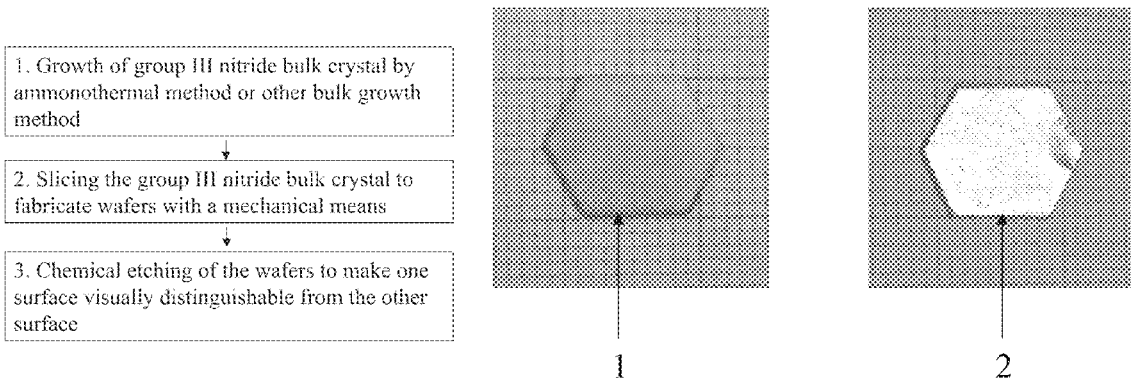
(57) **ABSTRACT**

The present invention discloses a group III nitride wafer such as GaN, AlN, InN and their alloys having one surface visually distinguishable from the other surface. After slicing of the wafer from a bulk crystal of group III nitride with a mechanical method such as multiple wire saw, the wafer is chemically etched so that one surface of the wafer is visually distinguishable from the other surface. The present invention also discloses a method of producing such wafers.

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